

### KTA1663 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.5 W ( $T_{amb}=25^{\circ}C$ )

Collector current

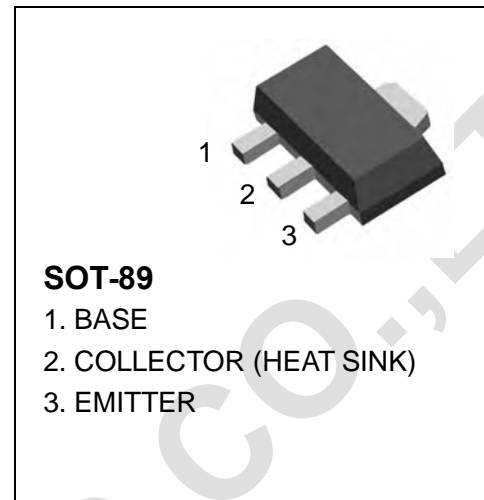
$I_{CM}$ : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$ : -35 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-30V, I_E=0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$		-0.1	$\mu A$
DC current gain	$H_{FE}$	$V_{CE}=-2V, I_C=-500mA$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-30mA$		-2.0	V
Base-Emitter saturation voltage	$V_{BE}$	$V_{CE}=-2V, I_C=500mA$		-1.0	
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-50mA$	80		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$		50	pF

#### CLASSIFICATION OF $h_{FE}$

Rank	O	Y
Range	100-200	160-320
Marking	HO	HY